

## SANYO Semiconductors DATA SHEET

### N-Channel Silicon MOSFET

# **CPH6415**— General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 1.8V drive.

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		4	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	16	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	3.8	5.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2A, V <sub>GS</sub> =4V		48	63	mΩ
	RDS(on)2	ID=1A, VGS=2.5V		63	88	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V		80	120	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		280		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		38		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		13		ns
Rise Time	tr	See specified Test Circuit.		50		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		33		ns
Fall Time	tf	See specified Test Circuit.		30		ns

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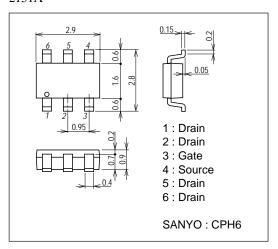
#### **CPH6415**

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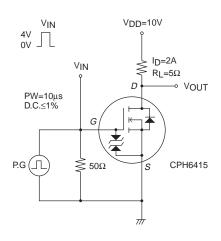
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oille
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4A		5.0		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4A		0.85		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4A		0.85		nC
Diode Forward Voltage	VSD	IS=4A, VGS=0		0.88	1.2	V

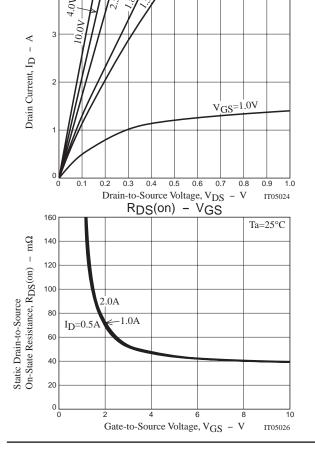
#### **Package Dimensions**

unit : mm 2151A

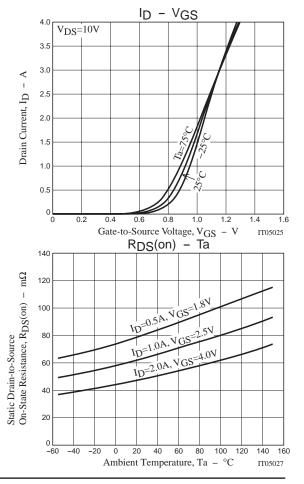


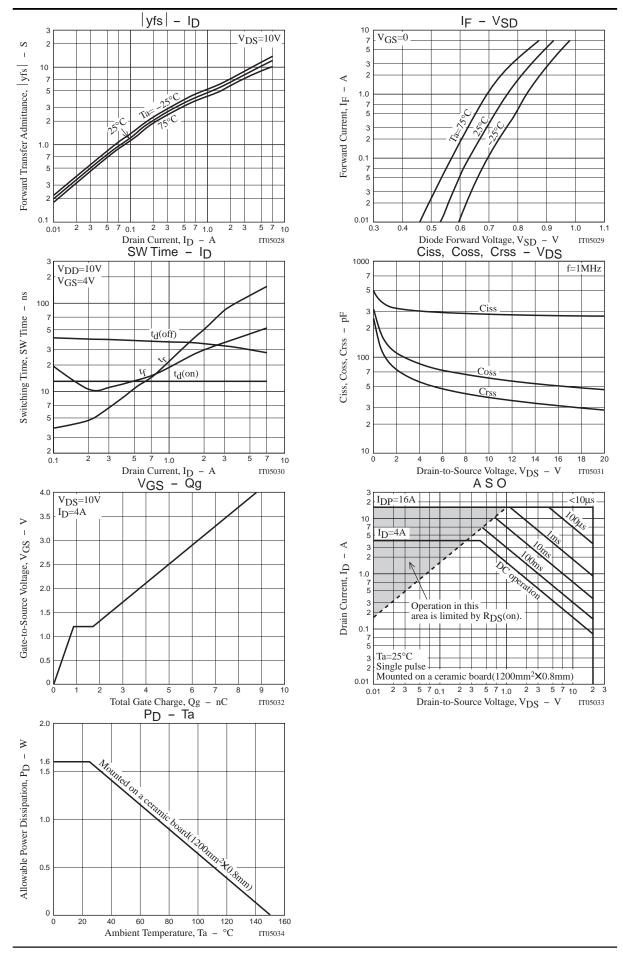
#### **Switching Time Test Circuit**





ID - VDS





Note on usage: Since the CPH6415 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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